

**MOTOROLA SEMICONDUCTOR TECHNICAL DATA**

T-33-11

**MRF455 MRF455A**

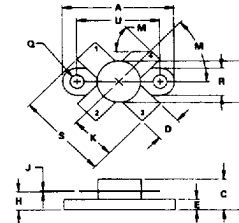
**The RF Line**

**NPN SILICON RF POWER TRANSISTORS**

... designed for power amplifier applications in industrial, commercial and amateur radio equipment to 30 MHz.

- Specified 12.5 Volt, 30 MHz Characteristics –  
 Output Power = 60 Watts  
 Minimum Gain = 13 dB  
 Efficiency = 55%

**60 W – 30 MHz  
 RF POWER TRANSISTORS  
 NPN SILICON**



NOTES  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M 1982.  
 2. CONTROLLING DIMENSION: INCH.



STYLE 1  
 PIN 1: EMITTER  
 2: BASE  
 3: EMITTER  
 4: COLLECTOR

**CASE 211-07  
 MRF455**

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	24.26	25.14	0.955	0.990
B	5.40	5.90	0.213	0.232
C	5.82	7.13	0.229	0.281
D	5.47	5.98	0.215	0.235
E	1.78	2.66	0.070	0.105
H	3.81	4.57	0.150	0.180
J	0.11	0.15	0.004	0.006
K	10.24	10.28	0.403	0.405
M	497	507	497	507
Q	2.80	3.30	0.110	0.130
R	6.23	6.47	0.245	0.255
S	20.07	20.67	0.790	0.810
U	18.29	18.54	0.720	0.730

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	18	Vdc
Collector-Emitter Voltage	V <sub>CES</sub>	36	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	15	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	175 1.0	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

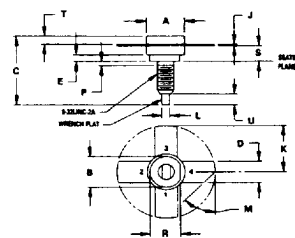
**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	1.0	°C/W

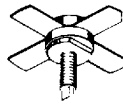
**MATCHING PROCEDURE**

In the push-pull circuit configuration it is preferred that the transistors are used as matched pairs to obtain optimum performance.

The matching procedure used by Motorola consists of measuring h<sub>FE</sub> at the data sheet conditions and color coding the device to predetermined h<sub>FE</sub> ranges within the normal h<sub>FE</sub> limits. A color dot is added to the marking on top of the cap. Any two devices with the same color dot can be paired together to form a matched set of units.



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**CASE 145A-09**

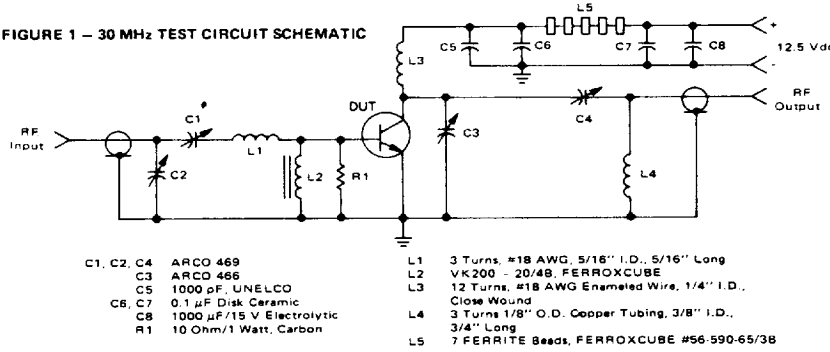
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.40	9.78	0.370	0.385
B	8.13	8.26	0.320	0.326
C	17.02	20.07	0.670	0.790
D	5.48	5.97	0.215	0.235
E	1.78	—	0.070	—
J	0.08	0.18	0.003	0.007
L	1.40	1.78	0.055	0.070
M	457 NOM	—	457 NOM	—
P	—	77	—	3.030
R	7.50	7.80	0.295	0.307
S	4.01	4.52	0.158	0.178
T	2.11	2.54	0.083	0.100
U	2.40	3.30	0.094	0.130

**ELECTRICAL CHARACTERISTICS** (TC = 25°C unless otherwise noted.)

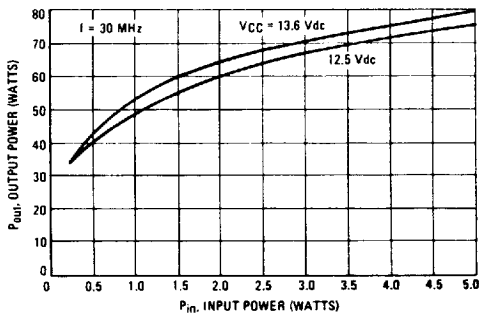
Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage ( $I_C = 100 \text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	18	—	—	Vdc
Collector-Emitter Breakdown Voltage ( $I_C = 50 \text{ mA}$ , $V_{BE} = 0$ )	$V_{(BR)CES}$	36	—	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \text{ mA}$ , $I_C = 0$ )	$V_{(BR)EBO}$	4.0	—	—	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 5.0 \text{ A}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$h_{FE}$	10	—	150	—
<b>DYNAMIC CHARACTERISTICS</b>					
Output Capacitance ( $V_{CB} = 12.5 \text{ Vdc}$ , $I_E = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{ob}$	—	—	250	pF
<b>FUNCTIONAL TESTS (Figure 1)</b>					
Common-Emitter Amplifier Power Gain ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$G_{pe}$	13	—	—	dB
Collector Efficiency ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$\eta$	55	—	—	%
Series Equivalent Input Impedance ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$Z_{in}$	—	1.66-j.844	—	Ohms
Series Equivalent Output Impedance ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$Z_{out}$	—	1.73-j.188	—	Ohms
Parallel Equivalent Input Impedance ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$Z_{in}$	—	2.09/1030	—	$\Omega/pF$
Parallel Equivalent Output Impedance ( $V_{CC} = 12.5 \text{ Vdc}$ , $P_{out} = 60 \text{ W}$ , $f = 30 \text{ MHz}$ )	$Z_{out}$	—	1.75/330	—	$\Omega/pF$

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**FIGURE 1 - 30 MHz TEST CIRCUIT SCHEMATIC**



**FIGURE 2 - OUTPUT POWER versus INPUT POWER**



**FIGURE 3 - OUTPUT POWER versus SUPPLY VOLTAGE**

